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Data Sheet

LED Chip visible

EOLC-410-34

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Radiation	Type	Electrodes
ultraviolet	GaN / sapphire	P + N up

Diagram	Description
	<p>Description</p> <ul style="list-style-type: none"> - Substrate: sapphire, epitaxial layer: GaN based material - N bonding pad electrode: Au alloy - P bonding pad electrode: Au alloy

Maximum Ratings

T_{amb} = 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I _F			20	mA
Peak forward current	t _p ≤ 50 μs, t _p /T = 1/2	I _{FM}			100	mA

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 20 mA	V _F		3.5	3.8	V
Reverse current	V _R = 5 V	I _R			1	μA
Radiant power*	I _F = 20 mA	Φ _e	4		6	mW
Peak wavelength	I _F = 20 mA	λ _p	405	410	415	nm
FWHM	I _F = 20 mA	Δλ _{0.5}		30		nm

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire-bond side top

Art. No. 112 002



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.